

ABSTRACT

The present invention relates to the use of ternary nickel-containing metal alloys of the NiMR type (where M = Mo, W, Re or Cr, and R = B or P) deposited by an electroless process in semiconductor technology. In particular, the present invention relates to the use of these deposited ternary nickel-containing metal alloys as barrier material or as selective encapsulation material for preventing the diffusion and electromigration of copper in semiconductor components.

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